ABSTRACT

THIN FILM TRANSISTOR

A method is proposed for producing a thin-film transistor (TFT), the method comprising forming a substrate, applying a ZnO-based precursor solution onto the substrate to form a ZnO-based channel layer, annealing the channel layer, forming a source electrode and a drain electrode on the channel layer, forming a dielectric layer on the channel layer and forming a gate electrode on the dielectric layer.

[Figure 2]

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